

IN THE CLAIMS:

No claims have been canceled and no claims have been amended herein. All of the pending claims 1 through 33 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as presented.

1. (Previously presented) A method for forming an assembly including semiconductor devices in stacked arrangement, comprising:
applying substantially a predetermined volume of adhesive material to an active surface of a first semiconductor device; and
positioning a second semiconductor device adjacent to the first semiconductor device without forcing adhesive material from beyond the active surface of the first semiconductor device, the adhesive material securing the second semiconductor device to the first semiconductor device, with the predetermined volume spacing a surface of the second semiconductor device a predetermined distance apart from the active surface of the first semiconductor device.
2. (Previously presented) The method of claim 1, wherein applying comprises applying the adhesive material to the active surface of the first semiconductor device over which discrete conductive elements extend.
3. (Previously presented) The method of claim 2, wherein positioning comprises positioning the second semiconductor device at least partially over at least one discrete conductive element of the discrete conductive elements.
4. (Previously presented) The method of claim 3, wherein positioning comprises placing the second semiconductor device on the discrete conductive elements.

5. (Previously presented) The method of claim 4, wherein applying comprises introducing the adhesive material between at least the first semiconductor device and the second semiconductor device.

6. (Previously presented) The method of claim 5, wherein introducing includes forcing the surface of the second semiconductor device away from at least the first semiconductor device and spacing the surface of the second semiconductor device apart from the discrete conductive elements.

7. (Previously presented) The method of claim 5, wherein introducing includes substantially encapsulating portions of the discrete conductive elements located over the active surface of at least the first semiconductor device.

8. (Original) The method of claim 5, further comprising:
substantially hardening the adhesive material to at least a semisolid state to space the active surface of at least the first semiconductor device substantially the predetermined distance apart from the surface of the second semiconductor device.

9. (Previously presented) The method of claim 8, wherein substantially hardening comprises substantially curing the adhesive material.

10. (Previously presented) The method of claim 8, wherein substantially hardening includes decreasing a distance the active surface of the first semiconductor device is spaced apart from the surface of the second semiconductor device from substantially a set distance to substantially the predetermined distance.

11. (Previously presented) The method of claim 1, wherein applying comprises applying the adhesive material to the active surface of at least the first semiconductor device before the positioning.

12. (Previously presented) The method of claim 8, further comprising, upon positioning, using the adhesive material to draw the second semiconductor device toward at least the first semiconductor device until at least the first semiconductor device and the second semiconductor device are spaced substantially a set distance apart from one another.

13. (Original) The method of claim 1, further comprising:
substantially hardening the adhesive material to at least a semisolid state to space the surface of
at least the first semiconductor device substantially the predetermined distance apart from
the surface of the second semiconductor device.

14. (Previously presented) The method of claim 13, wherein substantially hardening comprises substantially curing the adhesive material.

15. (Previously presented) The method of claim 13, wherein substantially hardening includes decreasing a distance the active surface of at least the first semiconductor device is spaced apart from the surface of the second semiconductor device from substantially a set distance to substantially the predetermined distance.

16. (Previously presented) A method for forming a multi-chip module, comprising:
providing a substrate including a plurality of contact areas;
establishing electrical communication between the substrate and a first semiconductor device;
applying substantially a predetermined volume of adhesive material onto at least a surface of the
first semiconductor device; and
positioning a second semiconductor device adjacent to the first semiconductor device without
forcing adhesive material from beyond the active surface of the first semiconductor
device, the adhesive material securing the second semiconductor device to the first
semiconductor device and spacing the surface of the second semiconductor device
substantially a predetermined distance apart from the surface of the first semiconductor
device.

17. (Previously presented) The method of claim 16, wherein applying is effected
following establishing.

18. (Previously presented) The method of claim 17, wherein positioning follows
applying.

19. (Previously presented) The method of claim 17, wherein applying follows
positioning.

20. (Previously presented) The method of claim 17, wherein positioning comprises
positioning the second semiconductor device over the first semiconductor device and at least
partially over at least one discrete conductive element protruding above the surface of the first
semiconductor device.

21. (Previously presented) The method of claim 16, wherein establishing electrical communication comprises:
placing discrete conductive elements between bond pads of the first semiconductor device and corresponding contact areas of the plurality of contact areas of the substrate to electrically connect the bond pads to the corresponding contact areas, the discrete conductive elements extending partially over the surface of the first semiconductor device.
22. (Previously presented) The method of claim 21, wherein placing discrete conductive elements comprises at least one of wire bonding bond pads to corresponding contact areas, tape-automated bonding bond pads to corresponding contact areas, and thermocompression bonding leads to bond pads.
23. (Original) The method of claim 21, further comprising:
encapsulating at least portions of the first semiconductor device, the second semiconductor device, the discrete conductive elements, and the substrate.
24. (Previously presented) The method of claim 16, wherein positioning the second semiconductor device comprises positioning the second semiconductor device onto the predetermined volume of adhesive material.
25. (Previously presented) The method of claim 16, further comprising using the predetermined volume of adhesive material to draw the second semiconductor device toward the first semiconductor device with the second semiconductor device spaced substantially a set distance apart from the first semiconductor device.
26. (Previously presented) The method of claim 16, wherein applying substantially the predetermined volume of adhesive material is effected following positioning of the second semiconductor device.

27. (Previously presented) The method of claim 26, wherein applying substantially the predetermined volume of adhesive material comprises introducing adhesive material between the first semiconductor device and the second semiconductor device.

28. (Previously presented) The method of claim 27, wherein introducing electrically isolates discrete conductive elements protruding from the first semiconductor device from the surface of the second semiconductor device.

29. (Previously presented) The method of claim 27, wherein introducing pushes the second semiconductor device away from the first semiconductor device to substantially the predetermined distance.

30. (Previously presented) The method of claim 27, wherein introducing coats at least portions of discrete conductive elements located adjacent to the surface of the second semiconductor device.

31. (Original) The method of claim 16, further comprising:
substantially hardening the adhesive material to at least a semisolid state to space the surface of the first semiconductor device apart from the surface of the second semiconductor device by substantially the predetermined distance.

32. (Previously presented) The method of claim 31, wherein substantially hardening comprises substantially curing the adhesive material.

33. (Previously presented) The method of claim 31, further comprising:
decreasing a distance the surface of the first semiconductor device is spaced apart from the
surface of the second semiconductor device from substantially a set distance to
substantially the predetermined distance by substantially hardening.